Alexey Chernykh

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

30	353	11	18
papers	citations	h-index	g-index
33	442	2.7	3.44
ext. papers	ext. citations	avg, IF	L-index

#	Paper	IF	Citations
30	Electrical properties of EGa2O3 films grown by halide vapor phase epitaxy on sapphire with ECr2O3 buffers. <i>Journal of Applied Physics</i> , 2022 , 131, 215701	2.5	1
29	Structural and electrical properties of thick EGa2O3 grown on GaN/sapphire templates. <i>APL Materials</i> , 2022 , 10, 061102	5.7	1
28	1 GeV proton damage in EGa2O3. <i>Journal of Applied Physics</i> , 2021 , 130, 185701	2.5	1
27	Parasitic pl junctions formed at V-pit defects in p-GaN. Journal of Applied Physics, 2021 , 129, 155702	2.5	1
26	Experimental estimation of electronfiole pair creation energy in EGa2O3. <i>Applied Physics Letters</i> , 2021 , 118, 202106	3.4	8
25	Crystal orientation dependence of deep level spectra in proton irradiated bulk EGa2O3. <i>Journal of Applied Physics</i> , 2021 , 130, 035701	2.5	4
24	Halide Vapor Phase Epitaxy of In2O3 and (In1\(\mathbb{N}\)Gax)2O3 on Sapphire Substrates and GaN/Al2O3 Templates. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021 , 218, 2000442	1.6	2
23	Photosensitivity of Ga2O3 Schottky diodes: Effects of deep acceptor traps present before and after neutron irradiation. <i>APL Materials</i> , 2020 , 8, 111105	5.7	13
22	Anisotropy of hydrogen plasma effects in bulk n-type EGa2O3. <i>Journal of Applied Physics</i> , 2020 , 127, 175702	2.5	14
21	Pulsed fast reactor neutron irradiation effects in Si doped n-type EGa2O3. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 274001	3	13
20	Electric field dependence of major electron trap emission in bulk EGa2O3: PooleErenkel effect versus phonon-assisted tunneling. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 304001	3	9
19	Role of hole trapping by deep acceptors in electron-beam-induced current measurements in EGa2O3 vertical rectifiers. <i>Journal Physics D: Applied Physics</i> , 2020 , 53, 495108	3	11
18	Electrical Properties, Deep Trap and Luminescence Spectra in Semi-Insulating, Czochralski EGa2O3 (Mg). <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3019-Q3023	2	25
17	Fast-Neutron Detectors Based on Surface-Barrier GaAs Sensors with an Ultrahigh-Molecular-Weight Polyethylene Converter. <i>Instruments and Experimental Techniques</i> , 2019 , 62, 312-316	0.5	1
16	Defects at the surface of EGa2O3 produced by Ar plasma exposure. APL Materials, 2019, 7, 061102	5.7	25
15	Deep trap spectra of Sn-doped EGa2O3 grown by halide vapor phase epitaxy on sapphire. <i>APL Materials</i> , 2019 , 7, 051103	5.7	22
14	Electrical Properties, Deep Levels and Luminescence Related to Fe in Bulk Semi-Insulating EGa2O3 Doped with Fe. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, Q3091-Q3096	2	19

LIST OF PUBLICATIONS

13	Deep traps and persistent photocapacitance in E(Al0.14 Ga0.86)2O3/Ga2O3 heterojunctions. Journal of Applied Physics, 2019 , 125, 095702	2.5	1	
12	Testing of a Prototype Detector of Heavy Charged Particles Based on Diamond Epitaxial Films Obtained by Gas-Phase Deposition. <i>Instruments and Experimental Techniques</i> , 2019 , 62, 473-479	0.5	Ο	
11	Hydrogen plasma treatment of EGa2O3: Changes in electrical properties and deep trap spectra. <i>Applied Physics Letters</i> , 2019 , 115, 032101	3.4	29	
10	Effects of Hydrogen Plasma Treatment Condition on Electrical Properties of EGa2O3. ECS Journal of Solid State Science and Technology, 2019, 8, P661-P666	2	4	
9	Detectors on the Basis of High-Purity Epitaxial GaAs Layers for Spectrometry of X and Gamma Rays. <i>Instruments and Experimental Techniques</i> , 2018 , 61, 665-672	0.5		
8	Electrical properties, structural properties, and deep trap spectra of thin EGa2O3 films grown by halide vapor phase epitaxy on basal plane sapphire substrates. <i>APL Materials</i> , 2018 , 6, 121110	5.7	26	
7	GaAs Schottky Barrier Detectors for Alpha-Particle Spectrometry at Temperatures up to 120°C. <i>Technical Physics Letters</i> , 2018 , 44, 942-945	0.7		
6	Electrical properties of bulk semi-insulating EGa2O3 (Fe). Applied Physics Letters, 2018, 113, 142102	3.4	59	
5	Hole traps and persistent photocapacitance in proton irradiated EGa2O3 films doped with Si. <i>APL Materials</i> , 2018 , 6, 096102	5.7	50	
4	Investigation of the thermal annealing effect on electrical properties of Ni/Au, Ni/Mo/Au and Mo/Au Schottky barriers on AlGaN/GaN heterostructures. <i>Journal of Physics: Conference Series</i> , 2017 , 816, 012039	0.3	4	
3	Mo/Al/Mo/Au-based ohmic contacts to AlGaN/GaN heterostructures. <i>Russian Microelectronics</i> , 2016 , 45, 402-409	0.5	1	
2	Schottky contacts to high-resistivity epitaxial GaAs layers for detectors of particles and X- or Fray photons. <i>Semiconductors</i> , 2012 , 46, 1066-1071	0.7	6	

Comparative Characteristics of GaAs Detectors and Silicon Pixel Detectors with Internal Amplification. *Materials Research Society Symposia Proceedings*, **2008**, 1108, 1